

CLAMP0524P

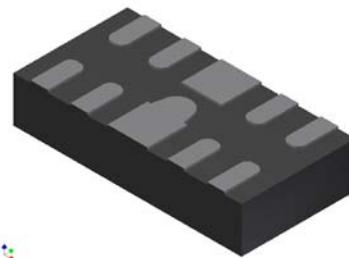
Ultra Low Capacitance Array for ESD Protection

The CLAMP0524P provides a typical line to line capacitance of 0.3pF between I/O pins and low insertion loss up to 3GHz providing greater signal integrity making it ideally suited for HDMI applications, such as Digital TVs, DVD players, Computing, set-top boxes and MDDI applications in mobile computing devices.

This series has been specifically designed to protect sensitive components which are connected to high-speed data and transmission lines from overvoltage caused by ESD(electrostatic discharge), CDE (Cable Discharge Events),and EFT (electrical fast transients).

Features

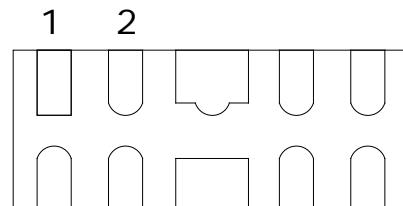
- Protects two or four I/O lines
- Low capacitance:0.3pf Typical between I/O channel
- Working voltages : 5V
- Low leakage current
- Response Time is < 1 ns
- Meets MSL 1 Requirements
- **Solid-state silicon avalanche technology**
- ROHS compliant
- WeiPan technology



Main applications

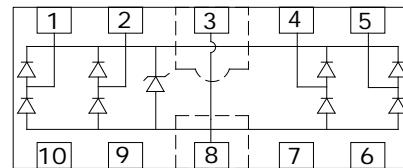
- High Definition Multi-Media Interface (HDMI)
- Digital Visual Interface (DVI)
- Display Port Interface
- Serial ATA
- PCI Express
- USB 1.1/2.0/3.0/OTG
- IEEE 1394 Firewire Ports
- Projection TV Monitors and Flat Panel Displays
- Notebook Computers
- Set Top Box
- Projection TV

DFN2510



Protection solution to meet

- IEC61000-4-2 (ESD) $\pm 15\text{kV}$ (air), $\pm 8\text{kV}$ (contact)
- IEC61000-4-4 (EFT) 40A (5/50ns)
- IEC61000-4-5 (Lightning) 5A (8/20 μs)



Ordering Information

Device	Qty per Reel	Reel Size
WPCLAMP0524P	3000	7 Inch

Maximum ratings (Tamb=25°C Unless Otherwise Specified)

Parameter	Symbol	Value	Unit
Peak Pulse Power (tp=8/20μs waveform)	P _{PPP}	150	Watts
Peak Pulse Current(tp=8/20μs waveform)	I _{PP}	5	A
ESD Rating per IEC61000-4-2:	Contact	8	KV
	Air	15	
Lead Soldering Temperature	T _L	260 (10 sec.)	°C
Operating Temperature Range	T _J	-55 ~ 150	°C
Storage Temperature Range	T _{STG}	-55 ~ 150	°C

Maximum ratings are those values beyond which device damage can occur. Maximum ratings applied to the device are individual stress limit values (not normal operating conditions) and are not valid simultaneously. If these limits are exceeded, device functional operation is not implied, damage may occur and reliability may be affected.

*Other voltages may be available upon request.

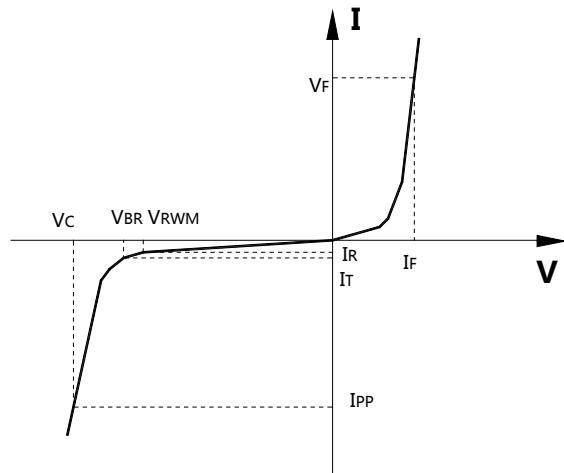
1. Nonrepetitive current pulse, per Figure 1.

Electrical characteristics (Tamb=25°C Unless Otherwise Specified)

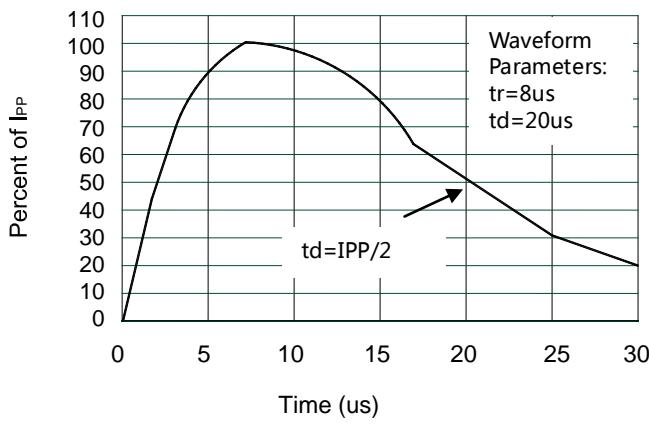
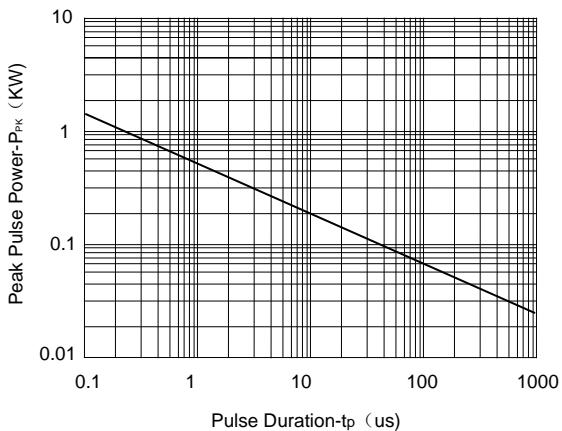
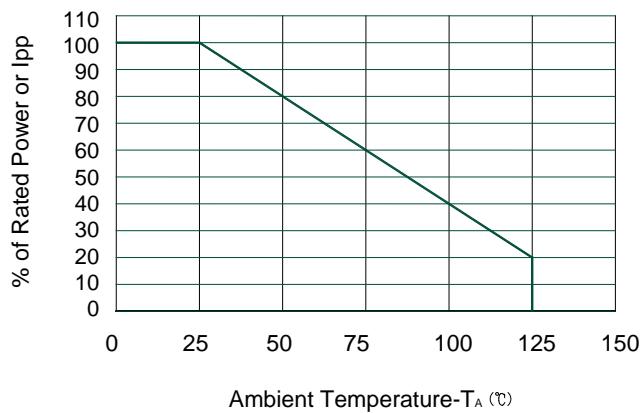
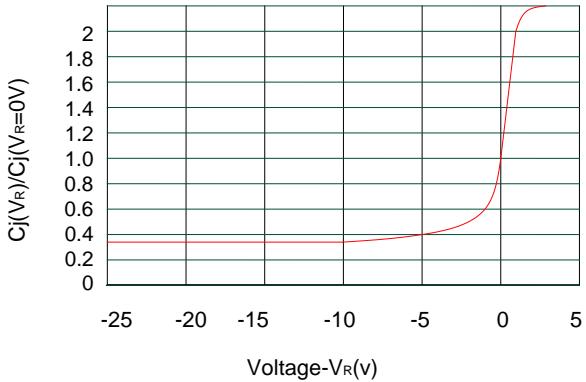
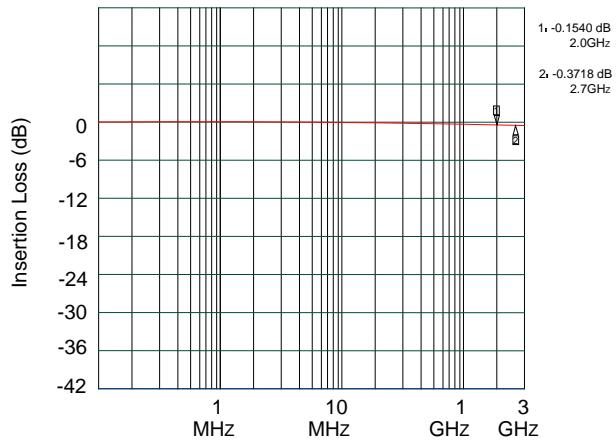
Symbol	Parameter	Conditions	Min.	Typ.	Max.	Units
V _{RWM}	Reverse Working Voltage	Any I/O to Ground			5.0	V
V _{BR}	Reverse Breakdown Voltage	IT = 1mA, Any I/O to Ground	6.0			V
I _R	Reverse Leakage Current	V _{RWM} = 5V, Any I/O to Ground			1	μA
V _F	Diode Forward Voltage	IF = 15mA		0.85	1.2	V
V _C	Clamping Voltage	I _{PP} = 1A, tp =8/20μs, any I/O pin to Ground			15.5	V
		I _{PP} = 5A, tp =8/20μs, any I/O pin to Ground			25	V
C _J	Junction Capacitance	V _R = 0V, f = 1MHz, between I/O pins		0.3	0.4	pF
		V _R = 0V, f = 1MHz, any I/O pin to Ground		0.45	0.8	pF

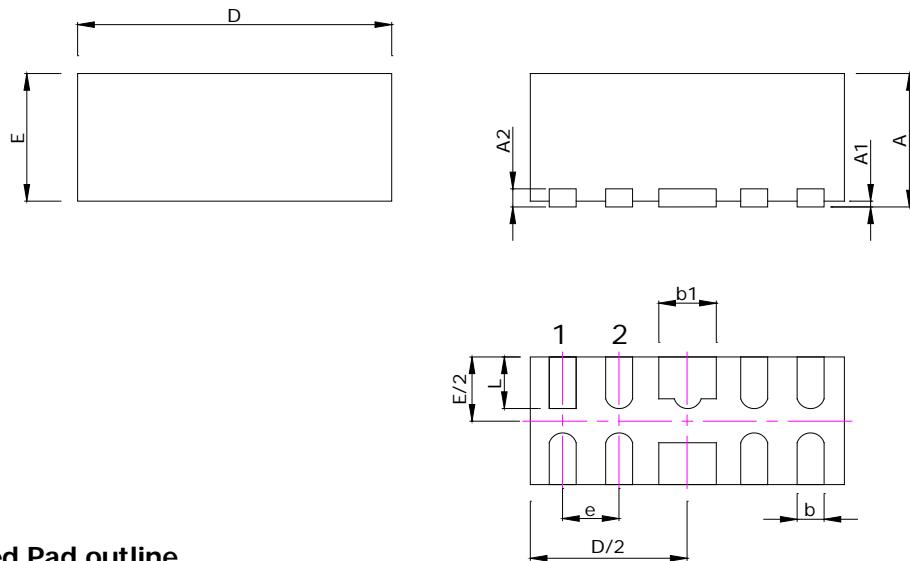
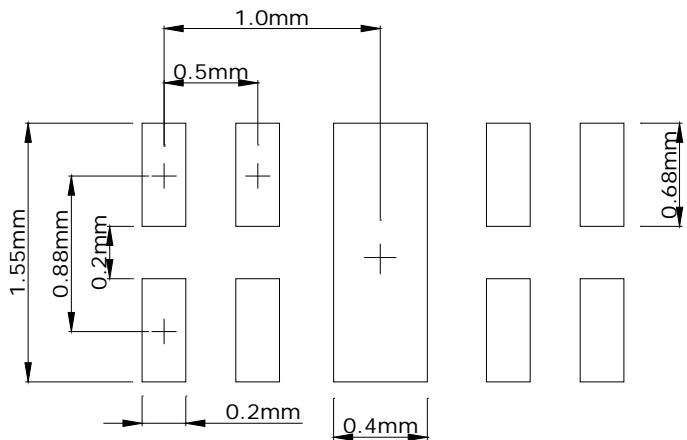
Junction capacitance is measured in VR=0V,F=1MHz

Symbol	Parameter
V _{RWM}	Working Peak Reverse Voltage
V _{BR}	Breakdown Voltage @ I _T
V _C	Clamping Voltage @ I _{PP}
I _T	Test Current
I _{RM}	Leakage current at V _{RWM}
I _{PP}	Peak pulse current
C _O	Off-state Capacitance
C _J	Junction Capacitance



Typical electrical characterist applications


Pulse Waveform

Non-Repetitive Peak Pulse Power vs. Pulse Time

Power Derating Curve

Junction Capacitance vs. Reverse Voltage

Insertion Loss S21

Package information**DFN2510****Recommended Pad outline**

Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	0.5	0.65	0.020	0.023
A1		0.05		0.002
A2	0.13			0.005
b	0.15	0.25	0.006	0.010
b1	0.35	0.45	0.014	0.018
D	2.40	2.60	0.094	0.102
E	0.90	1.10	0.035	0.043
e	0.5			0.020
L	0.30	0.43	0.012	0.017